



9/10/2012

**PRODUCT RELIABILITY REPORT  
FOR**

**DS1856M**

**Maxim Integrated Products**

**4401 South Beltwood Parkway  
Dallas, TX 75244-3292**

**Prepared by:**

**Don Lipps  
Manager, Reliability Engineering  
Maxim Integrated Products  
4401 South Beltwood Pkwy.  
Dallas, TX 75244-3292  
Email: don.lipps@maxim-ic.com  
ph: 972-371-3739**

**Conclusion:**

The following qualification successfully meets the quality and reliability standards required of all Maxim products:

DS1856M

In addition, Maxim's continuous reliability monitor program ensures that all outgoing product will continue to meet Maxim's quality and reliability standards. The current status of the reliability monitor program can be viewed at <http://www.maxim-ic.com/TechSupport/dsreliability.html>.

**Device Description:**

A description of this device can be found in the product data sheet. You can find the product data sheet at [http://dbserv.maxim-ic.com/l\\_datasheet3.cfm](http://dbserv.maxim-ic.com/l_datasheet3.cfm).

**Reliability Derating:**

The Arrhenius model will be used to determine the acceleration factor for failure mechanisms that are temperature accelerated.

$$AfT = \exp((Ea/k) * (1/Tu - 1/Ts)) = tu/ts$$

AfT = Acceleration factor due to Temperature  
tu = Time at use temperature (e.g. 55°C)  
ts = Time at stress temperature (e.g. 125°C)  
k = Boltzmann's Constant (8.617 x 10<sup>-5</sup> eV/°K)  
Tu = Temperature at Use (°K)  
Ts = Temperature at Stress (°K)  
Ea = Activation Energy (e.g. 0.7 ev)

The activation energy of the failure mechanism is derived from either internal studies or industry accepted standards, or activation energy of 0.7ev will be used whenever actual failure mechanisms or their activation energies are unknown. All deratings will be done from the stress ambient temperature to the use ambient temperature.

An exponential model will be used to determine the acceleration factor for failure mechanisms, which are voltage accelerated.

$$AfV = \exp(B * (Vs - Vu))$$

AfV = Acceleration factor due to Voltage  
Vs = Stress Voltage (e.g. 7.0 volts)  
Vu = Maximum Operating Voltage (e.g. 5.5 volts)  
B = Constant related to failure mechanism type (e.g. 1.0, 2.4, 2.7, etc.)

The Constant, B, related to the failure mechanism is derived from either internal studies or industry accepted standards, or a B of 1.0 will be used whenever actual failure mechanisms or their B are unknown. All deratings will be done from the stress voltage to the maximum operating voltage. Failure rate data from the operating life test is reported using a Chi-Squared statistical model at the 60% or 90% confidence level (Cf).

The failure rate, Fr, is related to the acceleration during life test by:

$$Fr = X / (ts * AfV * AfT * N * 2)$$

X = Chi-Sq statistical upper limit  
N = Life test sample size

Failure Rates are reported in FITs (Failures in Time) or MTTF (Mean Time To Failure). The FIT rate is related to MTTF by:

$$MTTF = 1/Fr$$

NOTE: MTTF is frequently used interchangeably with MTBF.

The calculated failure rate for this device/process is:

**FAILURE RATE:**                      **MTTF (YRS):**                      **53365**                      **FITS:**                      **2.1**  
**DEVICE HOURS:**                      **945392989**                      **FAILS:**                      **1**

Only data from Operating Life or similar stresses are used for this calculation.

The parameters used to calculate this failure rate are as follows:

**Cf: 60%**                      **Ea: 0.7**                      **B: 0**                      **Tu: 25 °C**                      **Vu: 5.5 Volts**

The reliability data follows. At the start of this data is the device information. The next section is the detailed reliability data for each stress. The reliability data section includes the latest data available and may contain some generic data. **Bold** Product Number denotes specific product data.

**Device Information:**

Process: SA E6W, 0.6um BiCMOS, 2 Poly, 2 Metal, EEPROM, 8 inch wafer  
 Passivation: TEOS Oxide-Nitride Passivation  
 Die Size: 100 x 131  
 Number of Transistors: 42342  
 Interconnect: Aluminum / 0.5% Copper  
 Gate Oxide Thickness: 150 Å

**ESD HBM**

DESCRIPTION	DATE	CODE/PRODUCT/LOT	CONDITION	READPOIN	QTY	FAILS	FA#
ESD SENSITIVITY	1221	<b>DS1856M</b>	ZJ280139AC JESD22-A114 HBM 500 VOLTS	1	PUL'S	5	0
ESD SENSITIVITY	1221	<b>DS1856M</b>	ZJ280139AC JESD22-A114 HBM 1000 VOLTS	1	PUL'S	5	0
ESD SENSITIVITY	1221	<b>DS1856M</b>	ZJ280139AC JESD22-A114 HBM 1500 VOLTS	1	PUL'S	5	0
ESD SENSITIVITY	1221	<b>DS1856M</b>	ZJ280139AC JESD22-A114 HBM 2000 VOLTS	1	PUL'S	5	0
ESD SENSITIVITY	1221	<b>DS1856M</b>	ZJ280139AC JESD22-A114 HBM 2500 VOLTS	1	PUL'S	5	0
<b>Total:</b>						<b>0</b>	

**LATCH-UP**

DESCRIPTION	DATE	CODE/PRODUCT/LOT	CONDITION	READPOIN	QTY	FAILS	FA#
LATCH-UP I	1221	<b>DS1856M</b>	ZJ280139AC JESD78A, I-TEST 25C 100mA			6	0
LATCH-UP I	1221	<b>DS1856M</b>	ZJ280139AC JESD78A, I-TEST 25C 250mA			6	0
LATCH-UP V	1221	<b>DS1856M</b>	ZJ280139AC JESD78A, V-SUPPLY TEST 25C			6	0
<b>Total:</b>						<b>0</b>	

